

DISCRIPTION

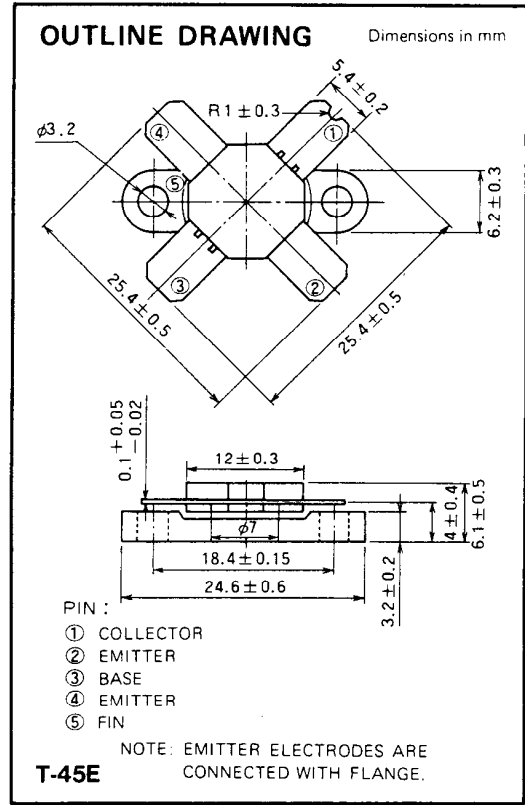
2SC3241 is a silicon NPN epitaxial planar type transistor specifically designed for high power amplifiers in HF band.

FEATURES

- High gain: $G_{pe} \geq 12.3\text{dB}$
@f = 30MHz, $V_{CC} = 12.5\text{V}$, $P_{in} = 4\text{W}$
- High ruggedness: Ability to withstand 20:1 load VSWR when operated at f = 30MHz, $V_{CC} = 15.2\text{V}$, $P_o = 75\text{W}$, $T_c = 25^\circ\text{C}$.
- Emitter ballasted construction
- Low thermal resistance ceramic package with flange
- Input-output impedance: $Z_{in} = 0.5 - j1.0(\Omega)$, $Z_{out} = 1.15 - j1.4(\Omega)$ @f = 30MHz, $V_{CC} = 12.5\text{V}$, $P_o = 75\text{W}$

APPLICATION

Output stage of transmitter in HF band SSB mobile radio sets.



ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CBO}	Collector to base voltage		50	V
V_{EBO}	Emitter to base voltage		5	V
V_{CEO}	Collector to emitter voltage	$R_{BE} = \infty$	20	V
I_C	Collector current		18	A
P_C	Collector dissipation	$T_a = 25^\circ\text{C}$	7.5	W
		$T_c = 25^\circ\text{C}$	180	W
T_j	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55 to 175	$^\circ\text{C}$
R_{th-a}	Thermal resistance	Junction to ambient	20	$^\circ\text{C/W}$
		Junction to case	0.83	$^\circ\text{C/W}$

Note. Above parameters are guaranteed independently.

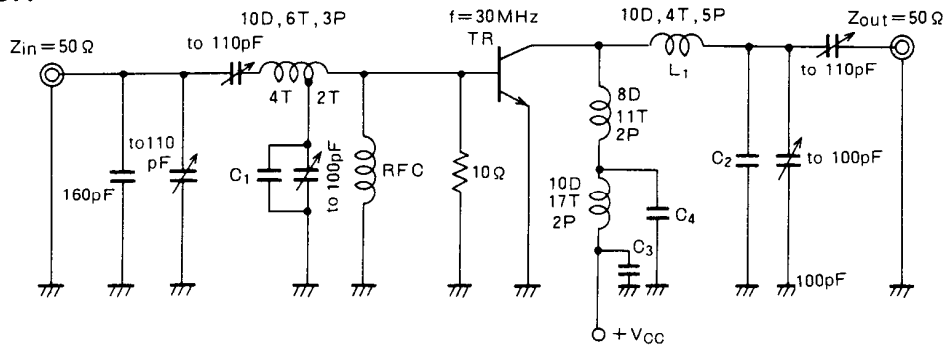
ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 20\text{mA}$, $I_C = 0$	5			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$, $I_E = 0$	50			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 100\text{mA}$, $R_{RE} = \infty$	20			V
I_{CBO}	Collector cutoff current	$V_{CE} = 25\text{V}$, $I_E = 0$			5	mA
I_{EBO}	Emitter cutoff current	$V_{EB} = 2\text{V}$, $I_C = 0$			4	mA
h_{FE}	DC forward current gain*	$V_{CE} = 10\text{V}$, $I_C = 0.1\text{A}$	10	50	180	—
P_O	Output power	$f = 30\text{MHz}$, $V_{CC} = 12.5\text{V}$, $P_{in} = 4\text{W}$	75	85		W
η_C	Collector efficiency		55	65		%

Note. * Pulse test, $P_w = 150\mu\text{s}$, duty = 5%.
Above parameters, ratings, limits and conditions are subject to change.

NPN EPITAXIAL PLANAR TYPE

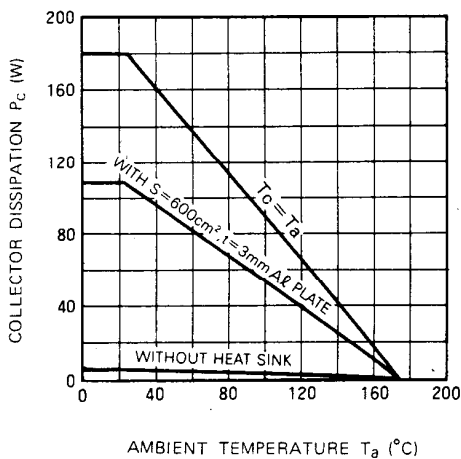
TEST CIRCUIT



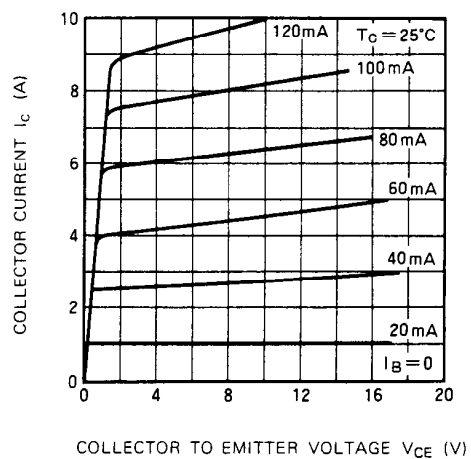
- C₁: 160pF, 160pF, 82pF in parallel
 - C₂: 82pF, 82pF, 82pF in parallel
 - C₃: 100pF, 4700pF, 4700pF, 0.22μF, 0.22μF, 33μF, 330μF in parallel
 - C₄: 100pF, 220pF, 4700pF, 0.1μF, 330μF in parallel
- NOTES: All coils but L₁ are made from 1.5φmm silver plated copper wire, L₁ is made from 2.3φmm copper wire.
 D: Inner diameter of coil P: Pitch of coil
 T: Turn number of coil Dimension is milli-meter
- RFC: 27 Turns 1φ enameled wire

TYPICAL PERFORMANCE DATA

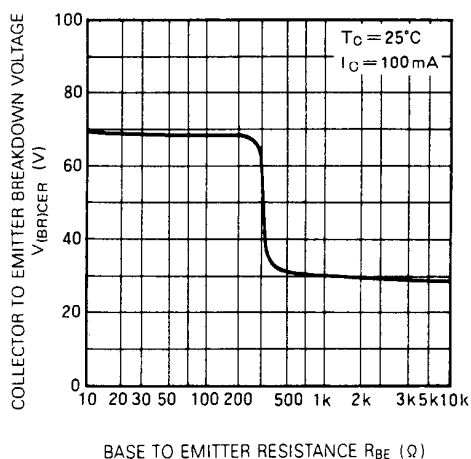
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



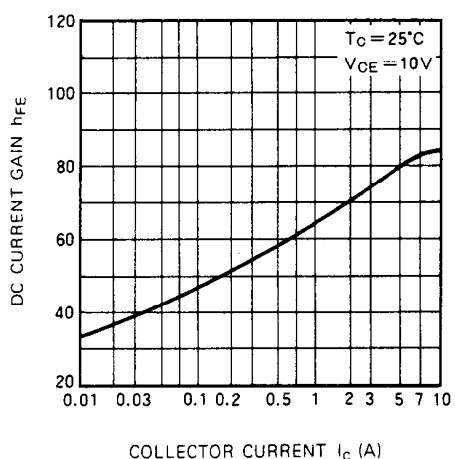
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE



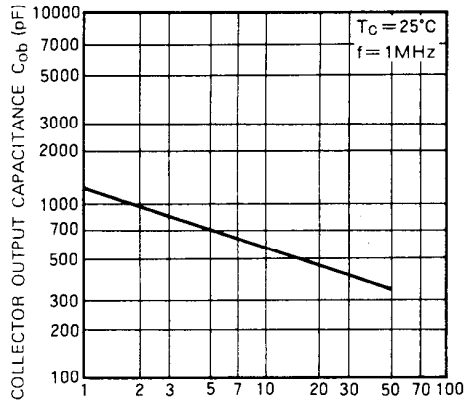
DC CURRENT GAIN VS. COLLECTOR CURRENT



MITSUBISHI RF POWER TRANSISTOR
2SC3241

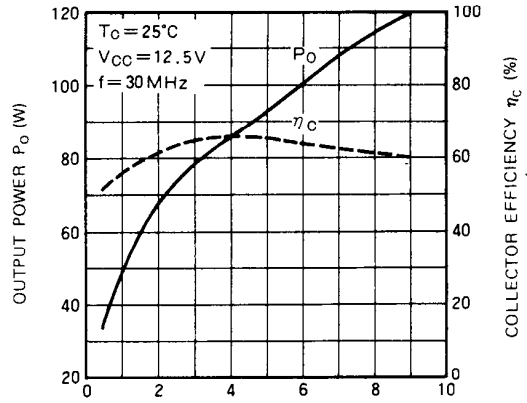
NPN EPITAXIAL PLANAR TYPE

COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



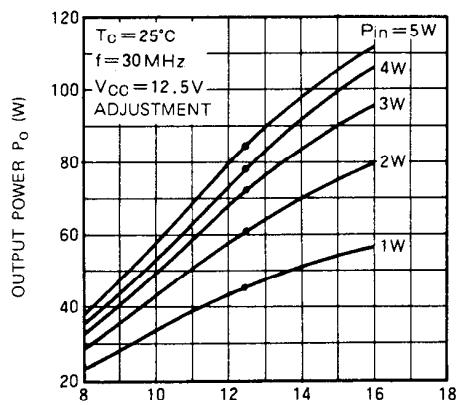
COLLECTOR TO BASE VOLTAGE V_{CB} (V)

OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER



INPUT POWER P_{in} (W)

OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE



COLLECTOR SUPPLY VOLTAGE V_{CC} (V)